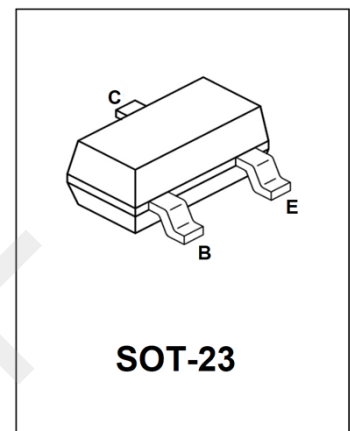


MMBT5551

- Complementary to: MMBT5401
- Package: SOT-23

Maximum Ratings (Ta = 25°)

Parameter	Symbol	Rating	Unit
Collector-base voltage	BV_{CBO}	180	V
Collector-emitter voltage	BV_{CEO}	160	V
Emitter-base voltage	BV_{EBO}	6	V
Collector current	I_{CM}	600	mA
Collector Power Dissipation	P_C	TO-90	625
		SOT-89	500
			mW
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-55~+150	°C



Electrical Characteristics (Ta=25°C)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV_{CBO}	$I_C=100\mu A, I_E=0$	180			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C=1mA, I_B=0$	160			V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E=100\mu A, I_C=0$	6			V
collector-base cut-off current	I_{CBO}	$V_{CB}=160V, I_E=0$			0.1	μA
collector-emitter cut-off current	I_{CEO}	$V_{CE}=140V, I_B=0$			0.1	μA
emitter-base cut-off current	I_{EBO}	$V_{EB}=5V, I_C=0$			0.1	μA
DC current gain	H_{FE1}	$V_{CE}=5V, I_B=1mA$	80			
	H_{FE2}	$V_{CE}=5V, I_B=10mA$	80		300	
	H_{FE3}	$V_{CE}=5V, I_B=50mA$	30			
collector-emitter saturation voltage	V_{CESAT}	$I_C=50mA, I_B=5mA$			0.25	V
Base-Emitter Saturation Voltage	V_{BESAT}	$I_C=50mA, I_B=5mA$			1.2	V
Transition frequency	f_T	$V_{CE}=10V, I_B=10mA$	100			MHz

Classification of H_{FE}

Rank	MMBT5551-O	MMBT5551-A	MMBT5551-B
Range	80-100	100-200	200-300